
2SC1472(K)

Silicon NPN Epitaxial, Darlington

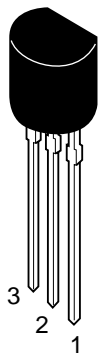
HITACHI

Application

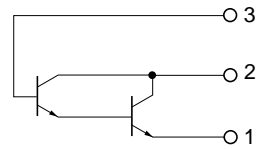
High gain amplifier

Outline

TO-92 (1)



- 1. Emitter
- 2. Collector
- 3. Base



2SC1472 (K)

Absolute Maximum Ratings (Ta = 25°C)

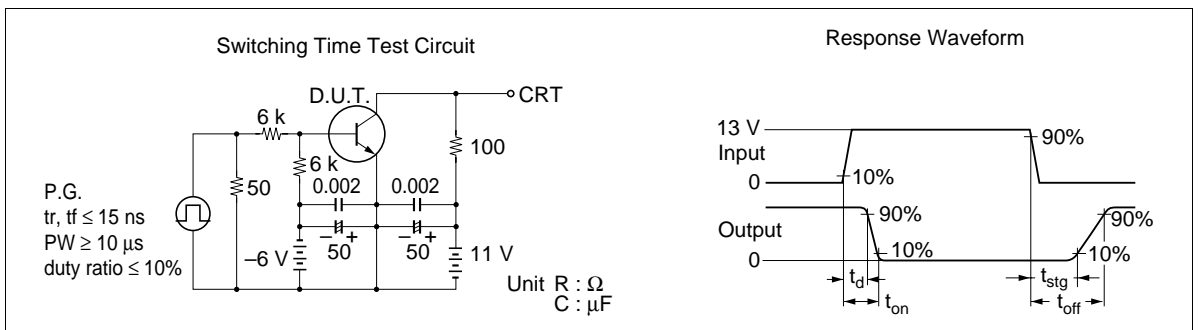
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	40	V
Collector to emitter voltage	V_{CEO}	30	V
Emitter to base voltage	V_{EBO}	10	V
Collector current	I_C	300	mA
Collector peak current	$i_{C(peak)}$	500	mA
Collector power dissipation	P_C	500	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

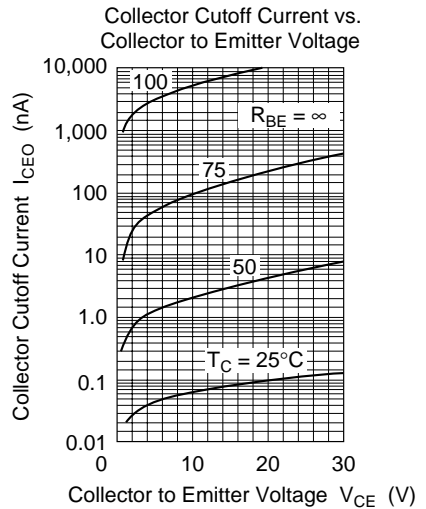
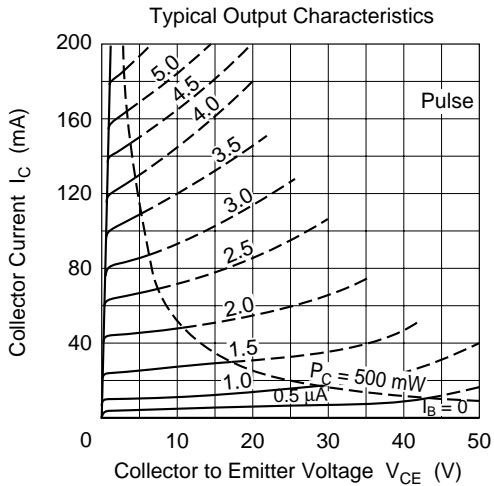
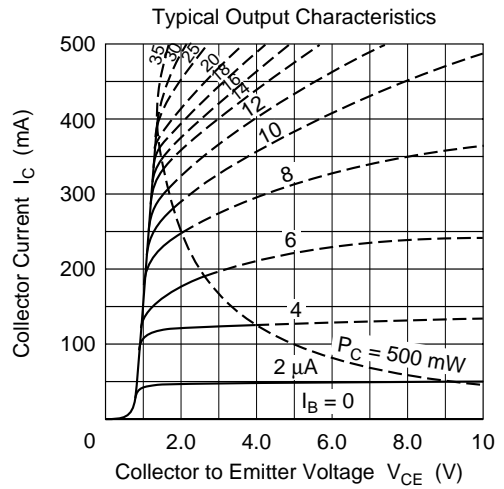
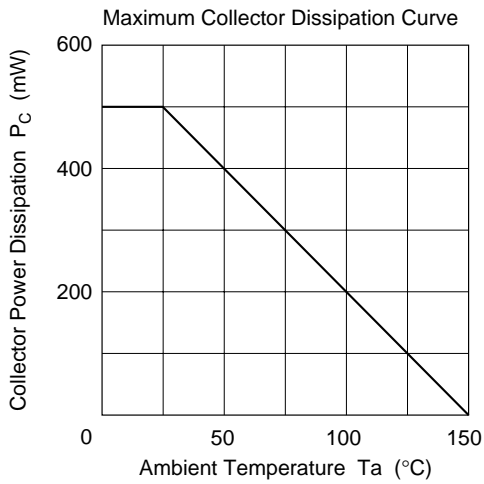
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Collector cutoff current	I_{CBO}	—	—	100	nA	$V_{CB} = 30 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	100	nA	$V_{EB} = 10 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE1}^{*1}	2000	—	100000		$I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}$
	h_{FE2}^{*1}	3000	—	—		$I_C = 100 \text{ mA}, V_{CE} = 5 \text{ V}$ (Pulse Test)
	h_{FE3}^{*1}	3000	—	—		$I_C = 400 \text{ mA}, V_{CE} = 5 \text{ V}$ (Pulse Test)
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$
Base to emitter voltage	$V_{BE(sat)}$	—	—	2.0	V	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$
Gain bandwidth product	f_T	50	—	—	MHz	$V_{CE} = 5 \text{ V}, I_C = 10 \text{ mA}$
Collector output capacitance	C_{ob}	—	—	10	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Turn on time	t_{on}	—	60	—	ns	$V_{CC} = 11 \text{ V}$ $I_C = 100 \text{ mA}, I_{B1} = 100 \text{ mA}$ $I_{B2} = -I_{B1}$
Turn off time	t_{off}	—	800	—	ns	
Storage time	t_{stg}	—	350	—	ns	

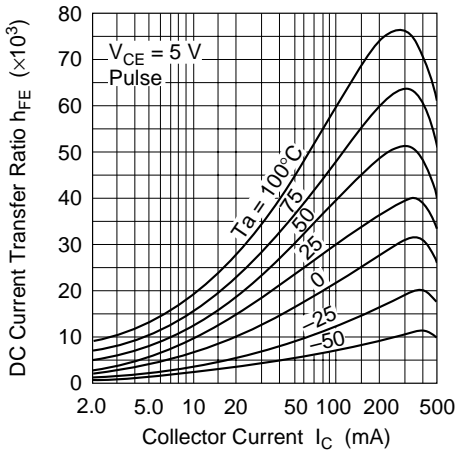
Note: 1. The 2SC1472(K) is grouped by h_{FE} as follows...

	A	B
h_{FE1}	2000 to 100000	5000 to 100000
h_{FE2}	3000 min	10000 min
h_{FE3}	3000 min	10000 min

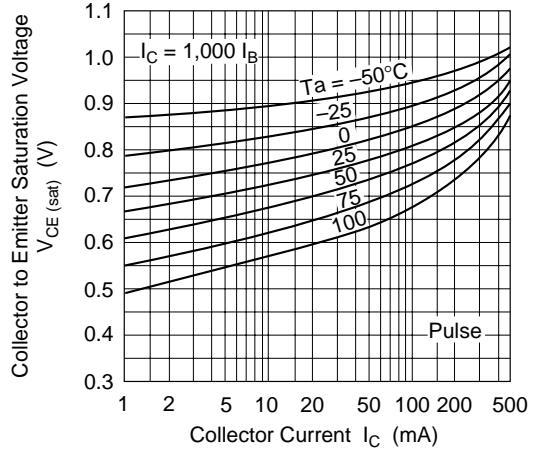




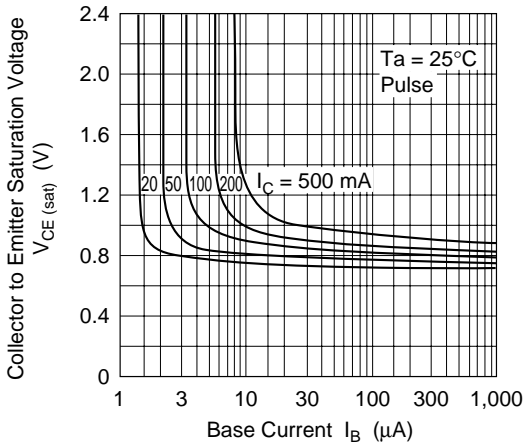
DC Current Transfer Ratio vs. Collector Current



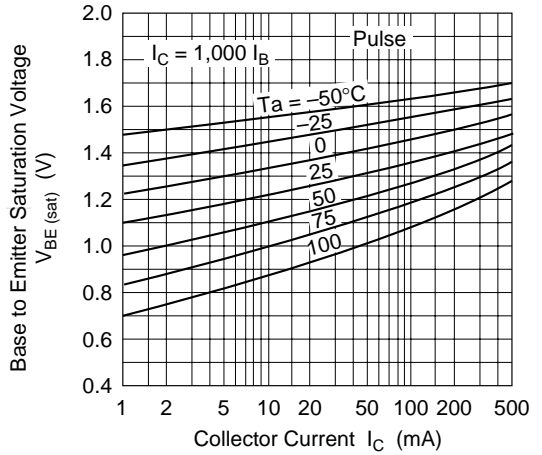
Collector to Emitter Saturation Voltage vs. Collector Current

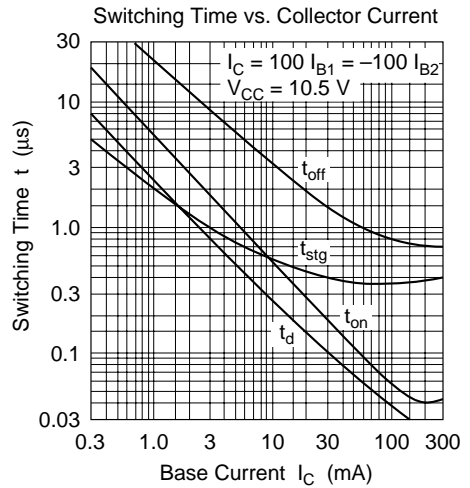
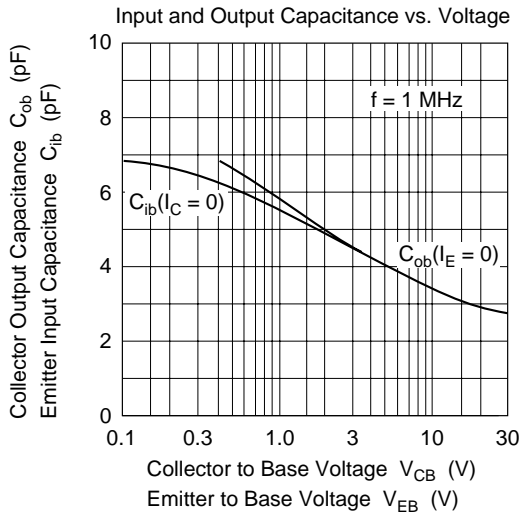


Collector to Emitter Saturation Voltage vs. Base Current

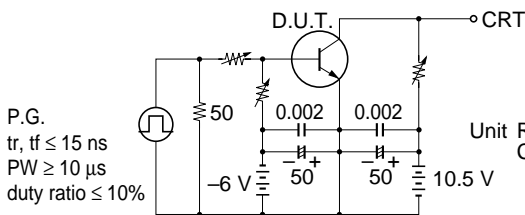


Base to Emitter Saturation Voltage vs. Collector Current

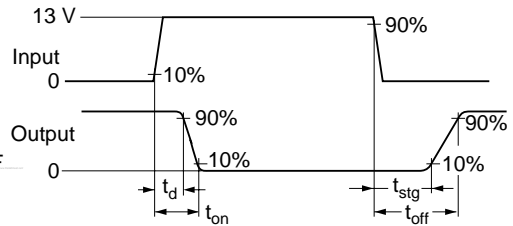


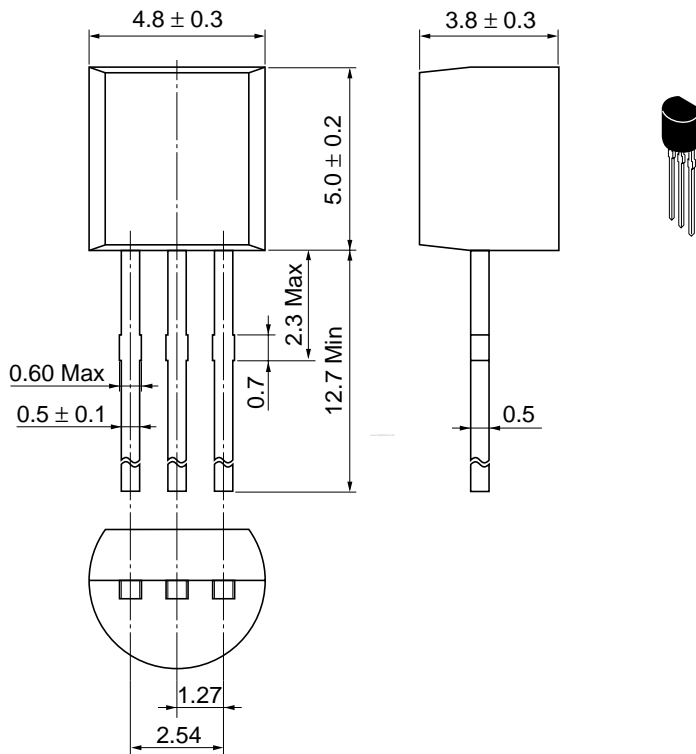


Switching Time Test Circuit



Response Waveform





Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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